



H7N0311LD, H7N0311LS, H7N0311LM

Silicon N Channel MOS FET High Speed Power Switching

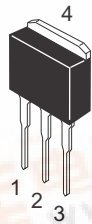
REJ03G1126-0500
(Previous: ADE-208-1423C)
Rev.5.00
Apr 07, 2006

Features

- Low on-resistance
 $R_{DS(on)} = 7.0\text{ m}\Omega$ typ.
- Low drive current

Outline

RENESAS Package code: PRSS0004AE-A
(Package name: LDPAK (L))



H7N0311LD

RENESAS Package code: PRSS0004AE-B
(Package name: LDPAK (S)-(1))



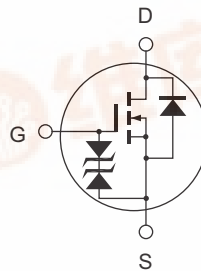
H7N0311LS

1. Gate
2. Drain
3. Source
4. Drain

RENESAS Package code: PRSS0004AE-C
(Package name: LDPAK (S)-(2))



H7N0311LM



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	45	A
Drain peak current	I _{D (pulse)} ^{Note 1}	180	A
Body to drain diode reverse drain current	I _{DR}	45	A
Channel dissipation	P _{ch} ^{Note 2}	60	W
Channel to case thermal impedance	θ _{ch-c}	2.08	°C/W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at Tc = 25°C

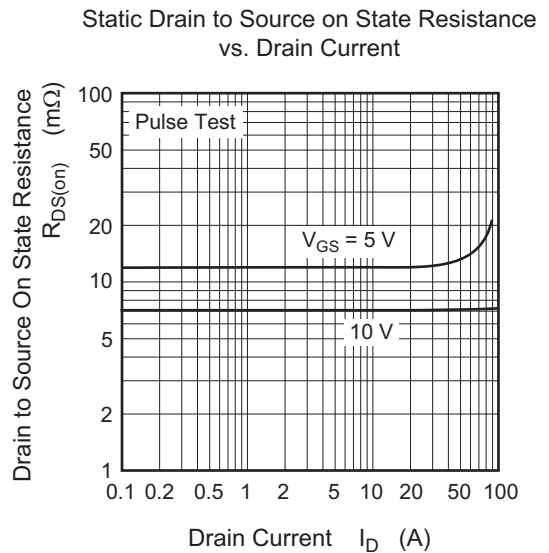
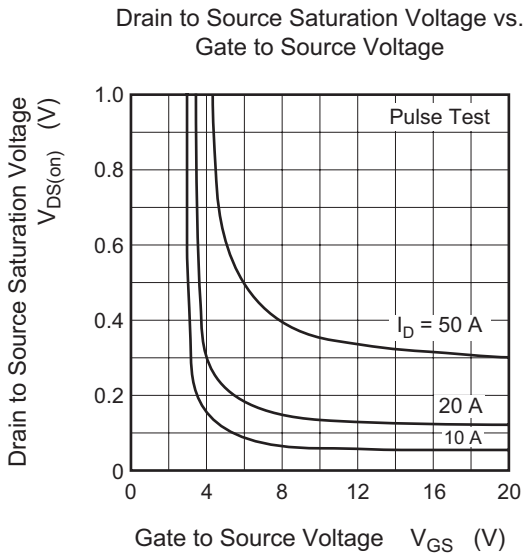
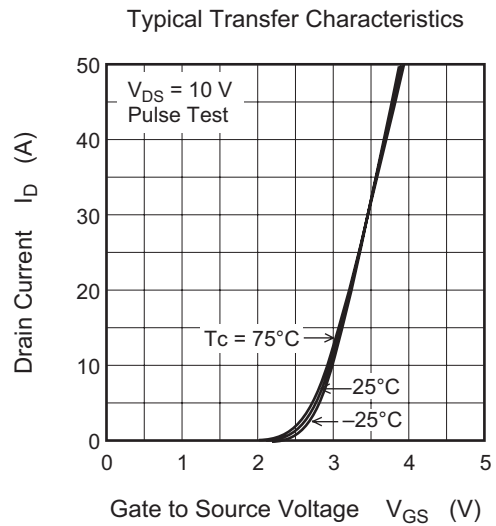
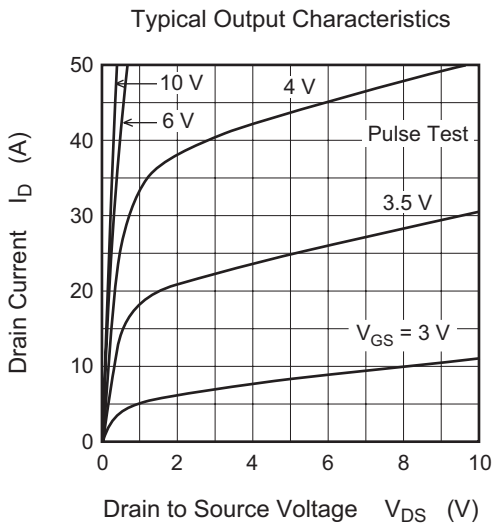
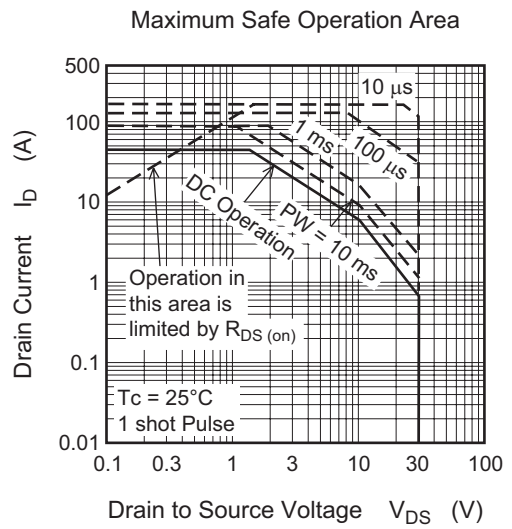
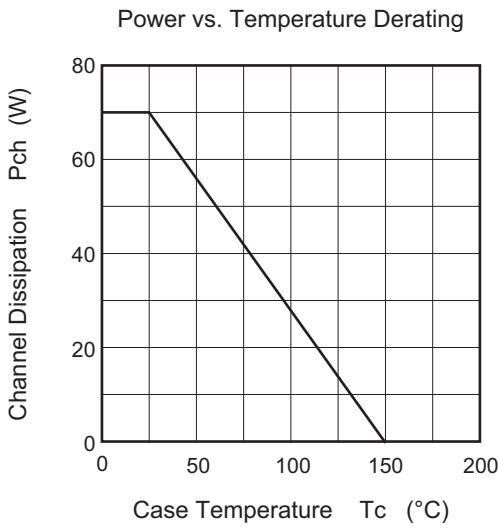
Electrical Characteristics

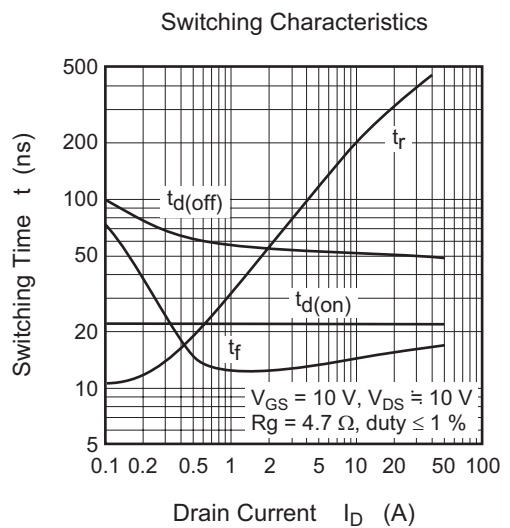
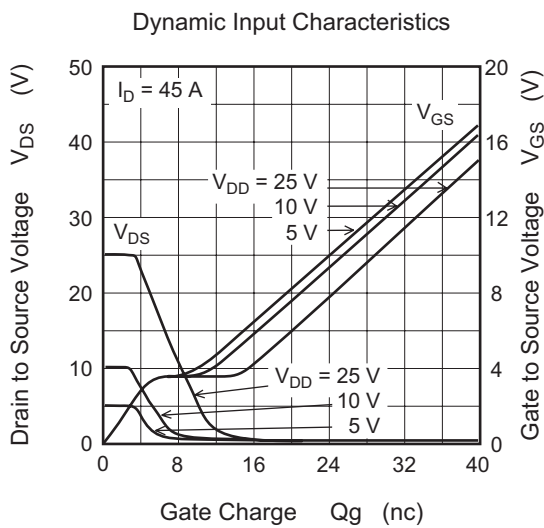
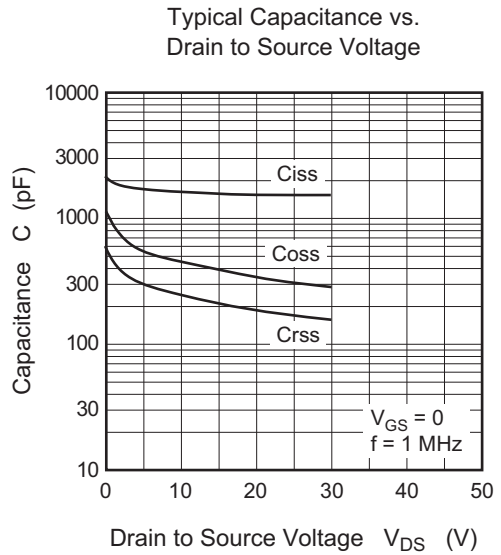
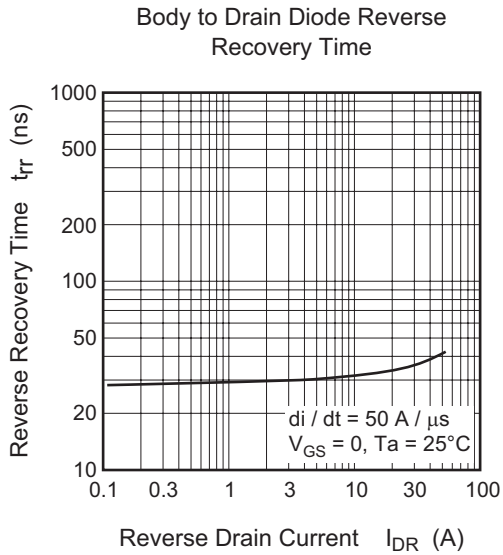
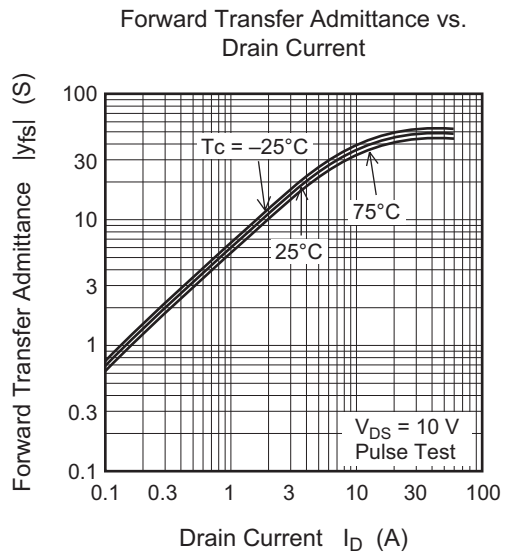
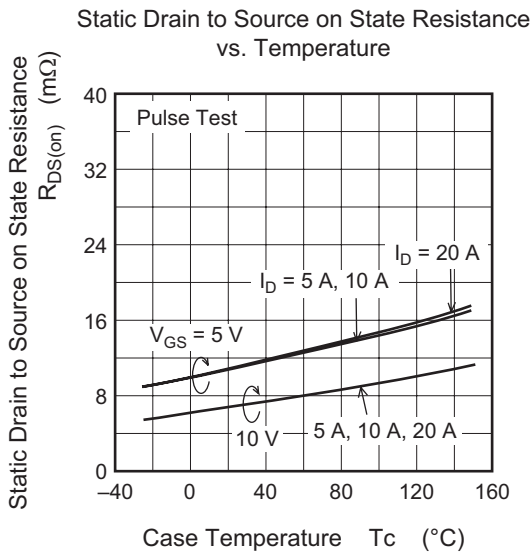
(Ta = 25°C)

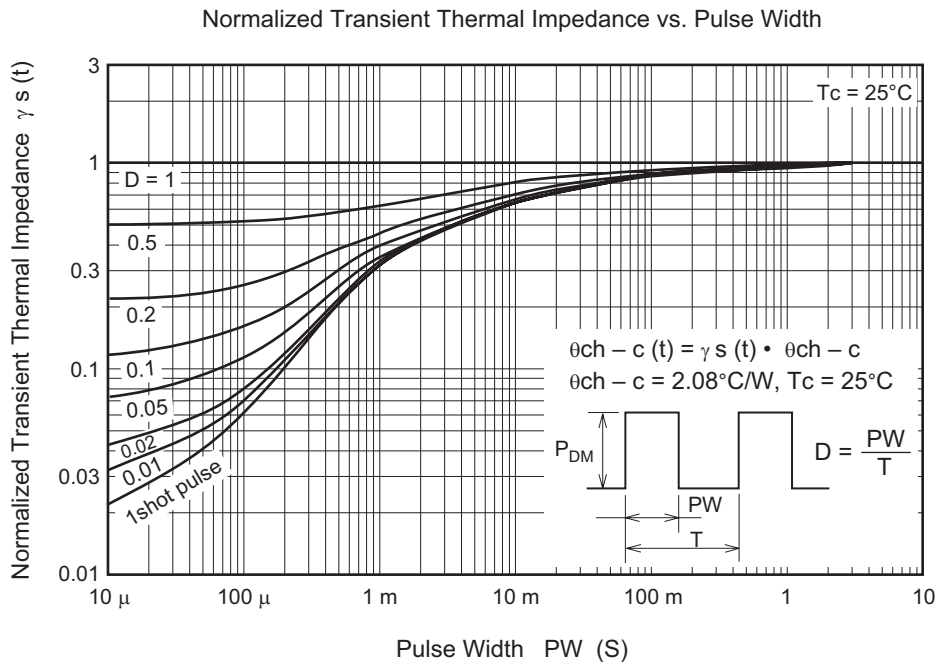
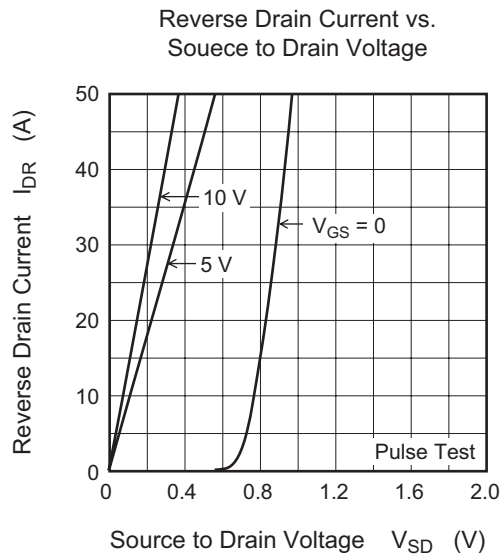
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	30	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	10	μA	V _{DS} = 30 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	1.0	—	2.5	V	I _D = 1 mA, V _{DS} = 10 V ^{Note 3}
Static drain to source on state resistance	R _{DS (on)}	—	7.0	8.8	mΩ	I _D = 22.5 A, V _{GS} = 10 V ^{Note 3}
		—	11	16	mΩ	I _D = 22.5 A, V _{GS} = 5 V ^{Note 3}
Forward transfer admittance	y _{fs}	27	45	—	S	I _D = 22.5 A, V _{DS} = 10 V ^{Note 3}
Input capacitance	C _{iss}	—	1650	—	pF	V _{DS} = 10 V
Output capacitance	C _{oss}	—	440	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	250	—	pF	f = 1 MHz
Total gate charge	Q _g	—	28	—	nC	V _{DD} = 10 V
Gate to source charge	Q _{gs}	—	6.0	—	nC	V _{GS} = 10 V
Gate to drain charge	Q _{gd}	—	5.4	—	nC	I _D = 45 A
Turn-on delay time	t _{d (on)}	—	22	—	ns	V _{GS} = 10 V, I _D = 22.5 A
Rise time	t _r	—	310	—	ns	R _L = 0.44 Ω
Turn-off delay time	t _{d (off)}	—	50	—	ns	R _g = 4.7 Ω
Fall time	t _f	—	16	—	ns	
Body to drain diode forward voltage	V _{DF}	—	0.93	—	V	I _F = 45 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	40	—	ns	I _F = 45 A, V _{GS} = 0 di _F /dt = 50 A/μs

Note: 3. Pulse test

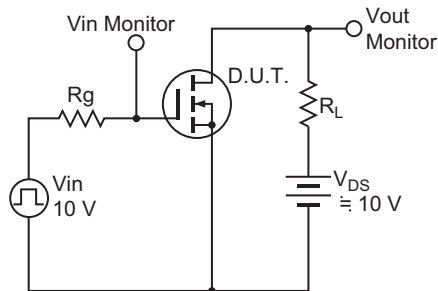
Main Characteristics



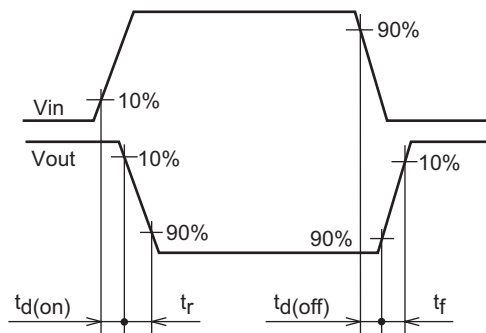




Switching Time Test Circuit



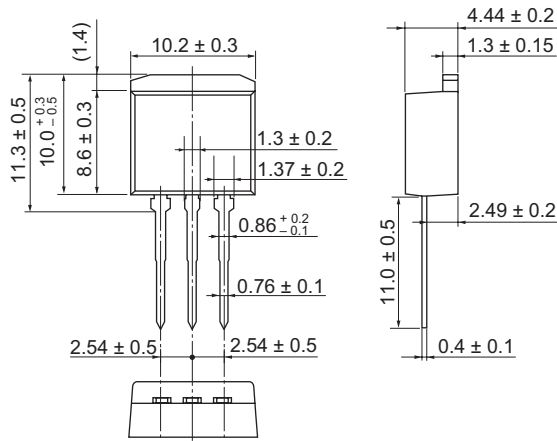
Switching Time Waveform



Package Dimensions

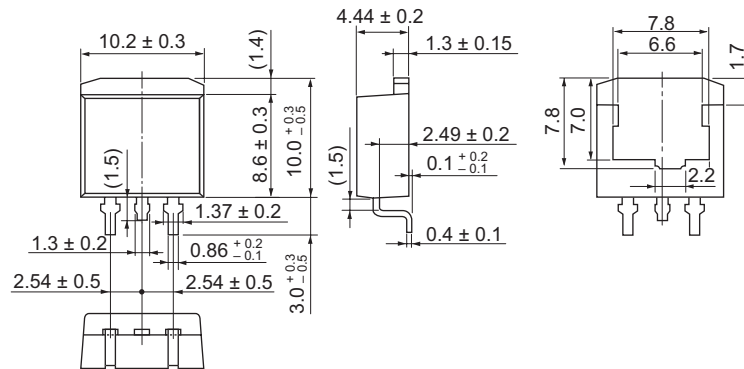
Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(L)	—	PRSS0004AE-A	LDBPAK(L) / LDBPAK(L)V	1.40g

Unit: mm

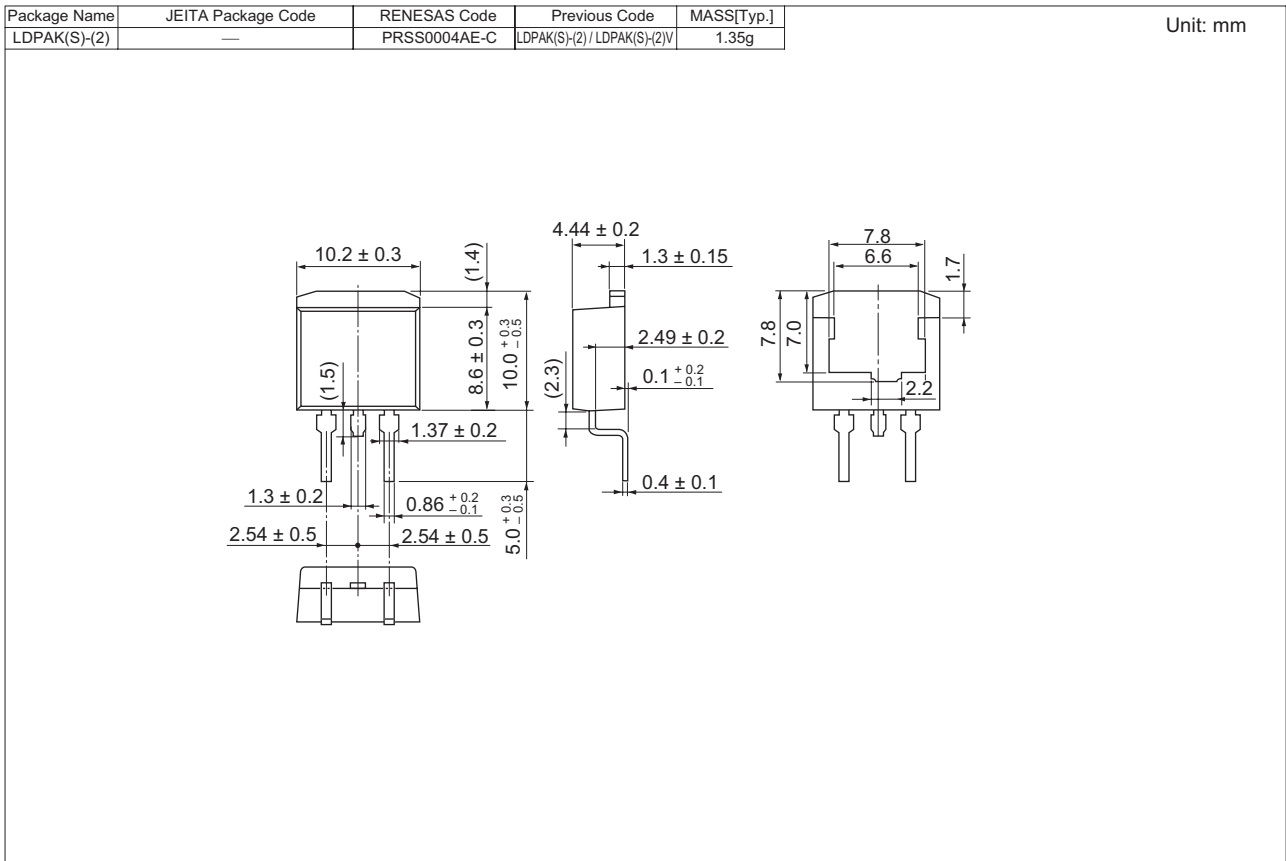


Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(1)	SC-83	PRSS0004AE-B	LDBPAK(S)-(1) / LDBPAK(S)-(1)V	1.30g

Unit: mm



H7N0311LD, H7N0311LS, H7N0311LM



Ordering Information

Part Name	Quantity	Shipping Container
H7N0311LD-E	500 pcs	Box (Conductive Sack)
H7N0311LSTL-E	1000 pcs	Taping
H7N0311LMTL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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